

# Silicon Carbide (SiC) Module – EliteSiC Power Module for OBC, 80 mohm, 1200 V, 20 A, Dual Half-Bridge, in APM32 Series

## NVXK2TR80WDT

### Features

- DIP Silicon Carbide H-Bridge Power Module for On-board Charger (OBC) for xEV Applications
- Creepage and Clearance per IEC 60664-1, IEC 60950-1
- Compact Design for Low Total Module Resistance
- Module Serialization for Full Traceability
- Lead Free, ROHS and UL94V-0 Compliant
- Automotive Qualified per AEC-Q101 and AQG324

### Typical Applications

- DC-DC and On-Board Charger in xEV Applications

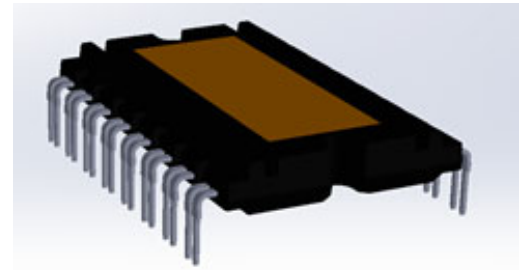
### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>	1200	V
Gate-to-Source Voltage	V <sub>GS</sub>	+25/-15	V
Recommended Operation Values of Gate-to-Source Voltage, T <sub>J</sub> ≤ 175°C	V <sub>GSop</sub>	+20/-5	V
Continuous Drain Current (Notes 1, 2)	I <sub>D</sub>	20	A
Power Dissipation (Note 1)			
Pulsed Drain Current (Note 3)	I <sub>DM</sub>	110	A
Single Pulse Surge Drain Current Capability	I <sub>DSC</sub>	266	A
Operating Junction Temperature	T <sub>J</sub>	-40 to 175	°C
Storage Temperature	T <sub>stg</sub>	-40 to 125	°C
Source Current (Body Diode) (Note 2)	I <sub>S</sub>	18	A
Single Pulse Drain-to-Source Avalanche Energy (Note 4)	E <sub>AS</sub>	180	mJ

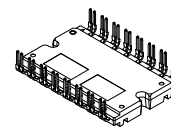
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Particular conditions specified determine thermal resistance values shown. Infinite heatsink with T<sub>C</sub> = 100°C for R<sub>θJC</sub>. For R<sub>ψJS</sub> assembled to 3 mm thick aluminum heatsink with infinite cooling bottom surface at 85°C, through 38 μm thick TIM with 6.5 W/mK thermal conductivity.
2. Qualified per ECPE Guideline AQG 324.
3. Repetitive rating limited by maximum junction temperature and transconductance.
4. E<sub>AS</sub> based on initial T<sub>J</sub> = 25°C, L = 1 mH, I<sub>AS</sub> = 19 A, V<sub>DD</sub> = 120 V, V<sub>GS</sub> = 18 V.

V <sub>(BR)DSS</sub>	R <sub>DS(on) Max</sub>	I <sub>D Max</sub>
1200 V	116 mΩ @ 20 V	20 A



APM32



APM32  
AUTOMOTIVE MODULE  
CASE MODHL

### MARKING DIAGRAM

NVXK2TR80WDT
ZZZ ATYWW
NNNNNNN

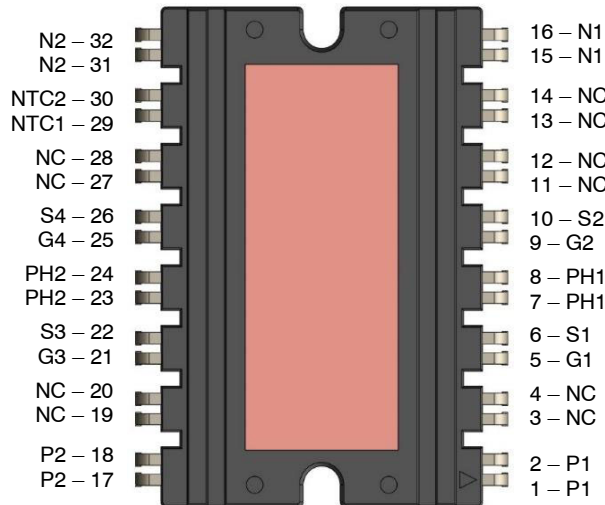
NVXK2TR80WDT = Specific Device Code  
 ZZZ = Lot ID  
 AT = Assembly Site & Test Location  
 Y = Year  
 W = Work Week  
 NNN = Serial Number

### ORDERING INFORMATION

Device	Package	Shipping
NVXK2TR80WDT	APM32 (Pb-Free)	10 ea / Tube

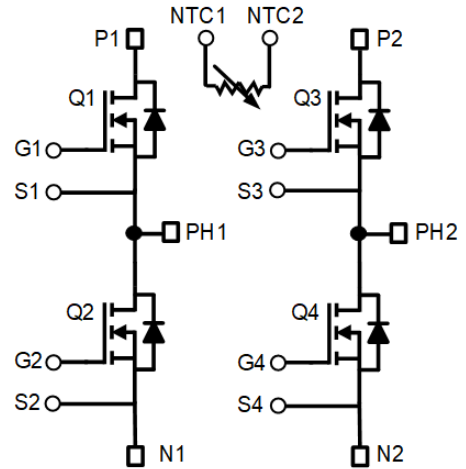
# NVXK2TR80WDT

## PIN CONFIGURATION



APM32

## INTERNAL EQUIVALENT CIRCUIT



SiC MOSFET H-Bridge Module

## PIN DESCRIPTION

Pin	Name	Pin Description
1, 2	P1	Intermediate DC Bus Plus1
5	G1	SiC MOSFET Gate1
6	S1	SiC MOSFET Source1
7, 8	PH1	Phase Connection1
9	G2	SiC MOSFET Gate2
10	S2	SiC MOSFET Source2
15, 16	N1	Intermediate DC Bus Minus1
17, 18	P2	Intermediate DC Bus Plus2
21	G3	SiC MOSFET Gate3
22	S3	SiC MOSFET Source3
23, 24	PH2	Phase Connection2
25	G4	SiC MOSFET Gate4
26	S4	SiC MOSFET Source4
29	NTC1	Negative Temperature Coefficient Thermistor1
30	NTC2	Negative Temperature Coefficient Thermistor2
31, 32	N2	Intermediate DC Bus Minus2
3, 4, 11, 12, 13, 14, 19, 20, 27, 28	NC	Not Connected pin

# NVXK2TR80WDT

## THERMAL CHARACTERISTICS (Note 1)

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-to-Case (Note 1)	$R_{\theta JC}$	1.41	1.84	$^{\circ}\text{C}/\text{W}$
Thermal Resistance Junction-to-Sink (Note 1)	$R_{\Psi JS}$	1.84	2.26	$^{\circ}\text{C}/\text{W}$

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	1200			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 1\text{ mA}$ , referenced to $25^{\circ}\text{C}$		500		$\text{mV}/^{\circ}\text{C}$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}, V_{DS} = 1200\text{ V}$	$T_J = 25^{\circ}\text{C}$		100	$\mu\text{A}$
			$T_J = 175^{\circ}\text{C}$		1	$\text{mA}$
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{GS} = +25/-15\text{ V}, V_{DS} = 0\text{ V}$			$\pm 1$	$\mu\text{A}$

## ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 5\text{ mA}$	1.8	3	4.3	V
Recommended Gate Voltage	$V_{GOP}$		-5		+20	V
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 20\text{ V}, I_D = 20\text{ A}, T_J = 25^{\circ}\text{C}$		80	116	$\text{m}\Omega$
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 20\text{ V}, I_D = 20\text{ A}, T_J = 175^{\circ}\text{C}$		150		$\text{m}\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS} = 20\text{ V}, I_D = 20\text{ A}$		11		S

## CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 800\text{ V}$		1154		$\text{pF}$
Output Capacitance	$C_{OSS}$			79		
Reverse Transfer Capacitance	$C_{RSS}$			7.9		
Total Gate Charge	$Q_G(TOT)$	$V_{GS} = -5/20\text{ V}, V_{DS} = 600\text{ V}, I_D = 20\text{ A}$		56		$\text{nC}$
Threshold Gate Charge	$Q_G(TH)$			10		
Gate-to-Source Charge	$Q_{GS}$			18		
Gate-to-Drain Charge	$Q_{GD}$			11		
Gate-Resistance	$R_G$		$V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1.2	

## INDUCTIVE SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -5/20\text{ V}, V_{DS} = 800\text{ V}, I_D = 20\text{ A}, R_G = 4.7\ \Omega,$ Inductive load		12		$\text{ns}$	
Rise Time	$t_r$			12			
Turn-Off Delay Time	$t_{d(OFF)}$			21			
Fall Time	$t_f$			9			
Turn-On Switching Loss	$E_{ON}$			135			$\mu\text{J}$
Turn-Off Switching Loss	$E_{OFF}$			46			$\mu\text{J}$
Total Switching Loss	$E_{tot}$			181			$\mu\text{J}$

## DRAIN-SOURCE DIODE CHARACTERISTICS

Continuous Drain-Source Diode Forward Current (Note 1)	$I_{SD}$	$V_{GS} = -5\text{ V}, T_J = 25^{\circ}\text{C}$			18	A
Pulsed Drain-Source Diode Forward Current (Note 3)	$I_{SDM}$	$V_{GS} = -5\text{ V}, T_J = 25^{\circ}\text{C}$			110	A
Forward Diode Voltage	$V_{SD}$	$V_{GS} = -5\text{ V}, I_{SD} = 10\text{ A}, T_J = 25^{\circ}\text{C}$		3.9		V

# NVXK2TR80WDT

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise stated) (continued)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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### DRAIN-SOURCE DIODE CHARACTERISTICS

Reverse Recovery Time	$t_{RR}$	$V_{GS} = -5\text{ V}$ , $dI_S/dt = 1000\text{ A}/\mu\text{s}$ , $I_{SD} = 20\text{ A}$		16.2		ns
Peak Reverse Recovery Current	$I_{RRM}$			7.6		A
Reverse Recovery Energy	$E_{REC}$			4.1		$\mu\text{J}$
Reverse Recovery Charge	$Q_{RR}$			61.6		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse test: pulse width  $\leq 300\ \mu\text{s}$ , duty ratio  $\leq 2\%$ .

### NTC THERMISTOR

Description	Type	Quantity	Specification
10 k $\Omega$ , $\pm 3\%$ Case Size 0603	Discrete	1	B Constants B <sub>25/50</sub> : 3590 B <sub>25/85</sub> = 3635 B <sub>25/100</sub> = 3650 $\pm 3\%$

# NVXK2TR80WDT

## TYPICAL CHARACTERISTICS

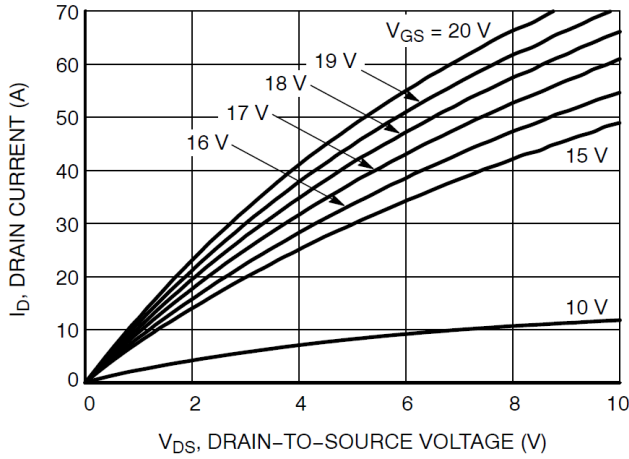


Figure 1. On-Region Characteristics

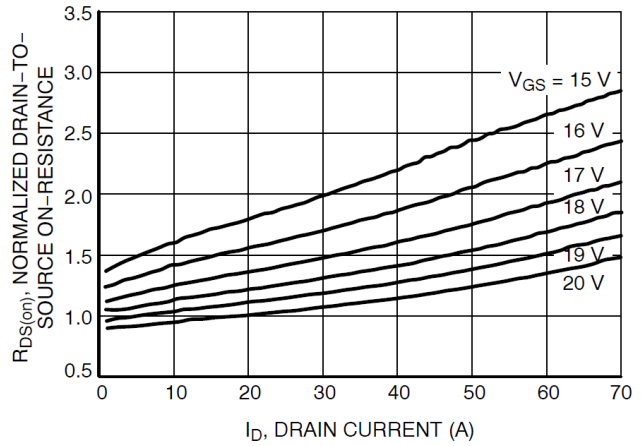


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

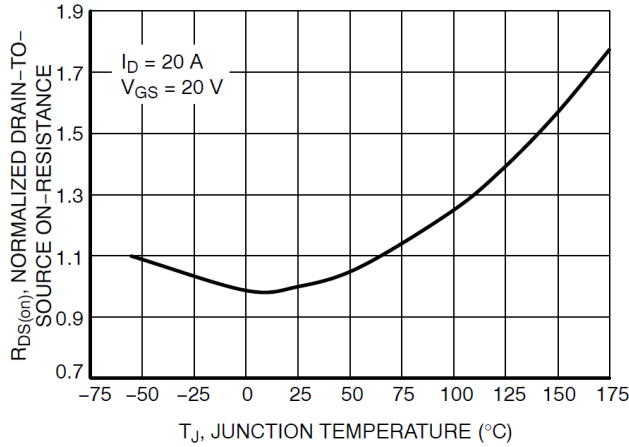


Figure 3. On-Resistance Variation with Temperature

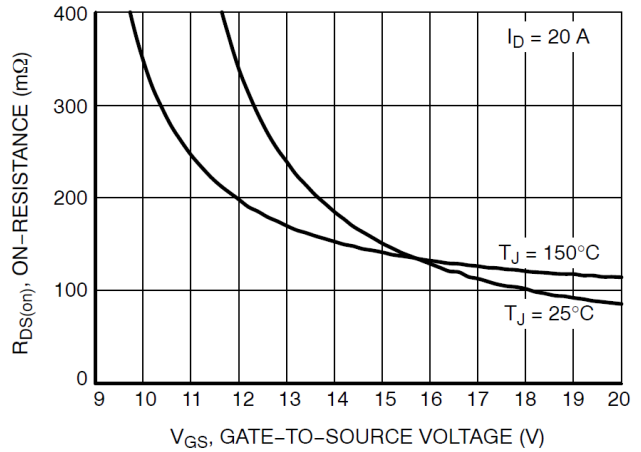


Figure 4. On-Resistance vs. Gate-to-Source Voltage

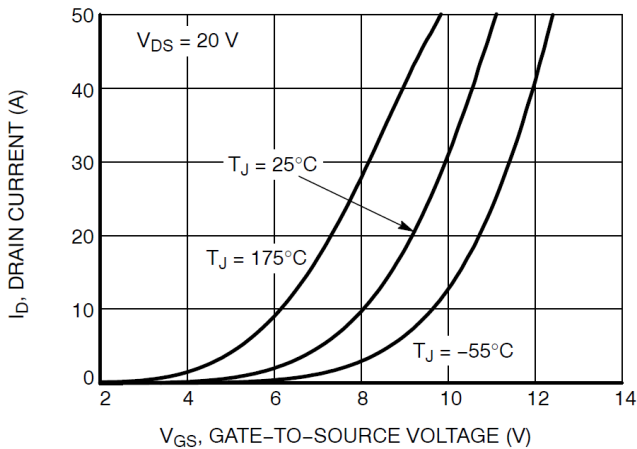


Figure 5. Transfer Characteristics

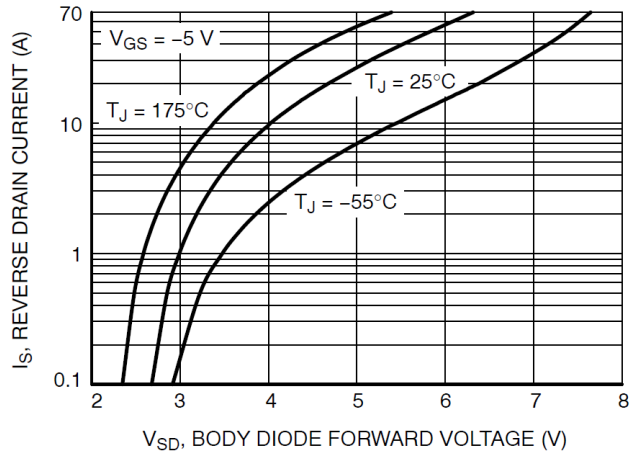
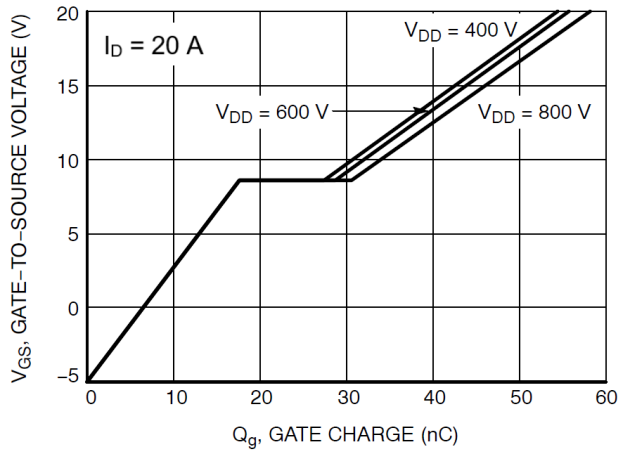


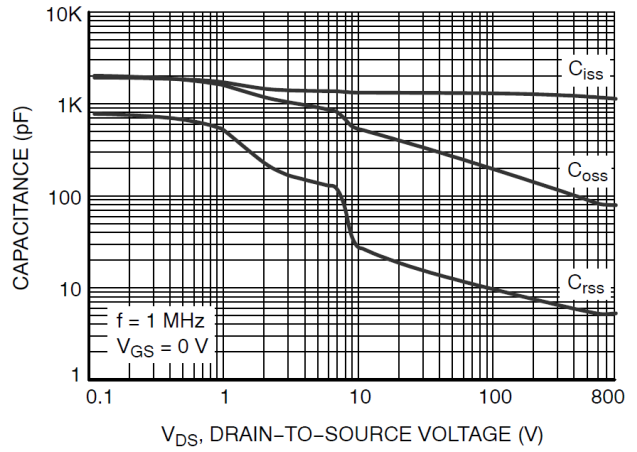
Figure 6. Diode Forward Voltage vs. Current

# NVXK2TR80WDT

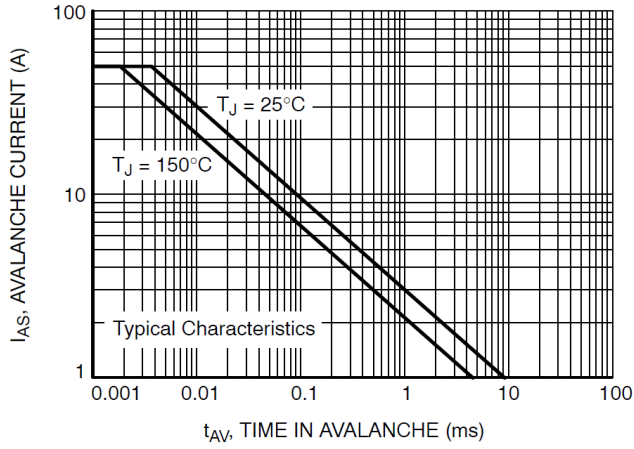
## TYPICAL CHARACTERISTICS (CONTINUED)



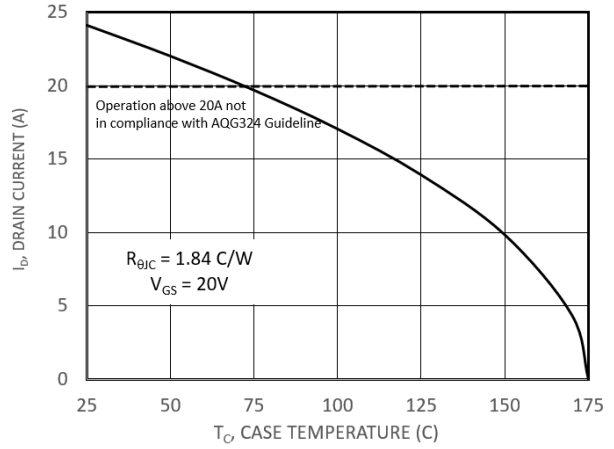
**Figure 7. Gate-to-Source Voltage vs. Total Charge**



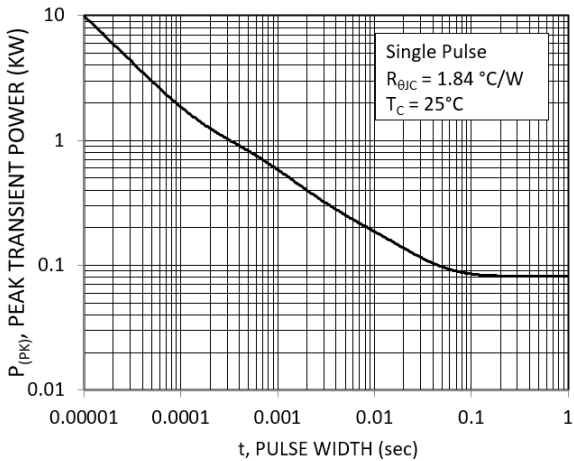
**Figure 8. Capacitance vs. Drain-to-Source Voltage**



**Figure 9. Unclamped Inductive Switching Capability**



**Figure 10. Maximum Continuous Drain Current vs. Case Temperature**



**Figure 11. Single Pulse Maximum Power Dissipation**

# NVXK2TR80WDT

## TYPICAL CHARACTERISTICS (CONTINUED)

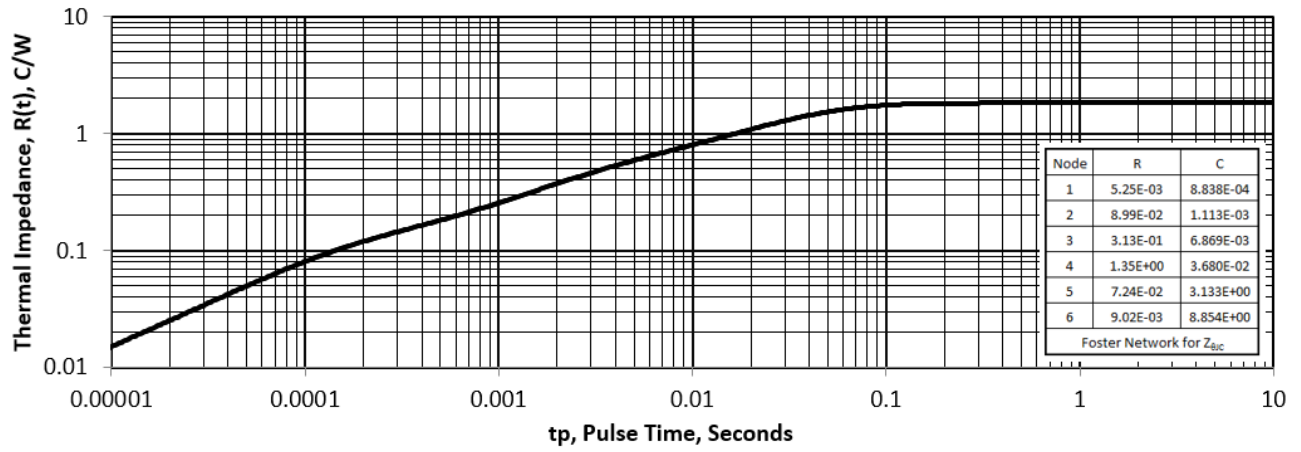
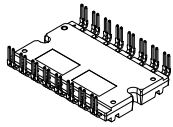


Figure 12. Thermal Response

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

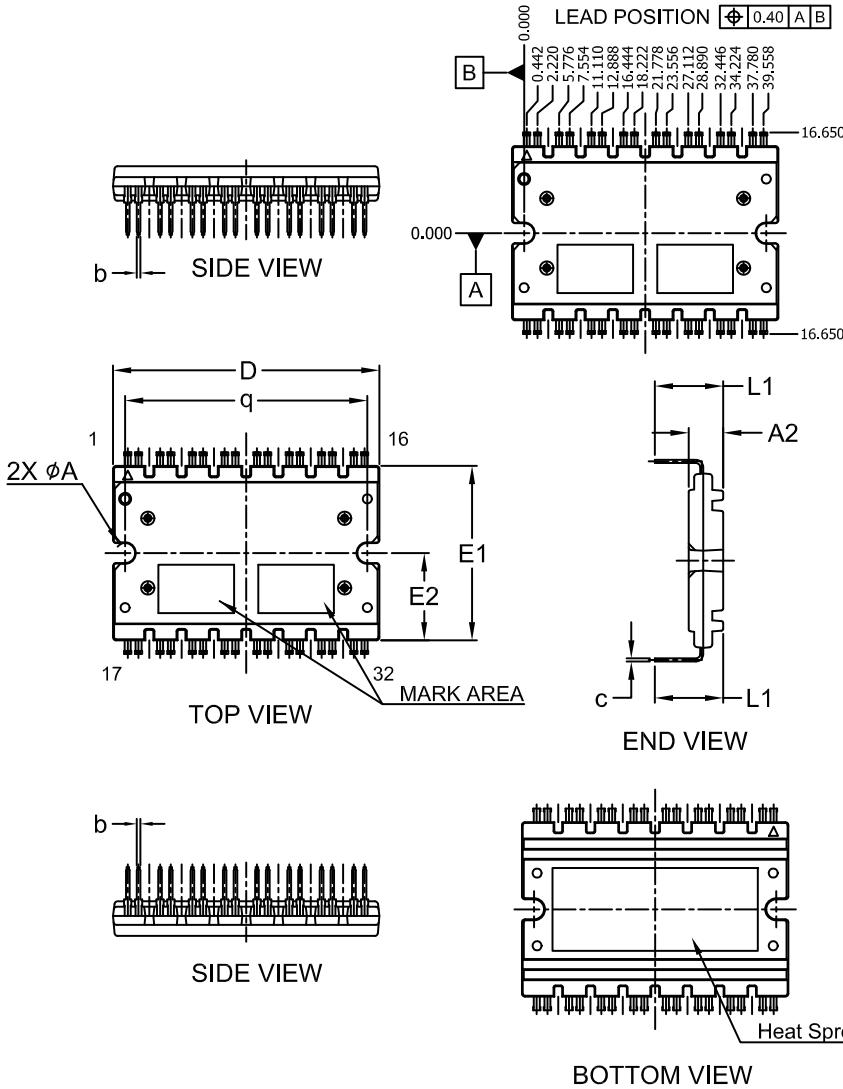


### APM32 AUTOMOTIVE MODULE

#### CASE MODHL

#### ISSUE B

DATE 05 APR 2022

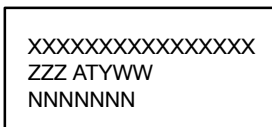


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A2	5.60	5.70	5.80
b	0.50	0.60	0.70
c	0.45	0.50	0.60
D	43.80	44.00	44.20
E1	28.60	28.80	29.00
E2	14.25	14.40	14.55
L1	11.00	11.30	11.60
q	39.85	40.00	40.15
$\phi A$	3.20	3.30	3.40

### GENERIC MARKING DIAGRAM\*



- XXXX = Specific Device Code
- ZZZ = Lot ID
- AT = Assembly & Test Location
- Y = Year
- W = Work Week
- NNN = Serial Number

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "μ", may or may not be present. Some products may not follow the Generic Marking.

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